FDPF44N25T

N-Channel UniFET™ MOSFET

250 V, 44 A, 69 mΩ

Features

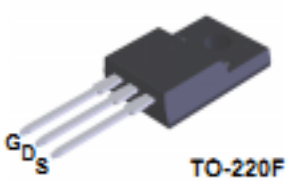
- $R_{DS(on)}$ = 69 mΩ (Max.) @ V_{GS} = 10 V, I_D = 22 A
- Low Gate Charge (Typ. 47 nC)
- Low C_{rss} (Typ. 60 pF)

Applications

- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

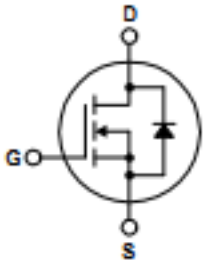
Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220F

TO-220F
LG-formed



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDPF44N25T FDPF44N25TRDTU	Unit
V_{DSS}	Drain-Source Voltage		250	V
I_D	Drain Current	• Continuous (T_C = 25°C) • Continuous (T_C = 100°C)	44* 26.4*	A A
I_{DM}	Drain Current	• Pulsed (Note 1)	176*	A
V_{GSS}	Gate-Source voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	2055	mJ
I_{AR}	Avalanche Current	(Note 1)	44	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	30.7	mJ
dv/dt	Peak Diode Recovery dv/d	(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) • Derate Above 25°C	38 0.3	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDPF44N25T FDPF44N25TRDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF44N25T	FDPF44N25T	TO-220F	Tube	N/A	N/A	50 units
FDPF44N25TRDTU	FDPF44N25T	TO-220F (LG-formed)	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA, T_J = 25°C	250	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C	--	0.25	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V V_{DS} = 200 V, T_C = 125°C	-- --	-- --	1 10	µA µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 22 A	--	0.058	0.069	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 22 A	--	32	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	2210	2870	pF
C_{oss}	Output Capacitance		--	450	585	pF
C_{rss}	Reverse Transfer Capacitance		--	60	90	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125 V, I_D = 44 A, R_G = 25 Ω (Note 4)	--	53	117	ns
t_r	Turn-On Rise Time		--	402	814	ns
$t_{d(off)}$	Turn-Off Delay Time		--	85	179	ns
t_f	Turn-Off Fall Time		--	112	234	ns
Q_g	Total Gate Charge	V_{DS} = 200 V, I_D = 44 A, V_{GS} = 10 V (Note 4)	--	47	61	nC
Q_{gs}	Gate-Source Charge		--	18	--	nC
Q_{gd}	Gate-Drain Charge		--	24	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	44	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	176	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 44 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 44 A, dI_F/dt = 100 A/µs	--	195	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.8	--	µC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 1.7 mH, I_{AS} = 44 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 44 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.